

10/825,120

MODIFIED PTO/SB/08 A & B (06-03)

Substitute for Form 1449 A & B/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Complete if Known

Application Number	[case serial number]
Confirmation Number	Not Assigned
Filing Date	April 16, 2004
First Named Inventor	Georg BASTIAN
Art Unit	Not Assigned
Examiner Name	Not Assigned
Attorney Docket Number	Q80758

Sheet 1 of 1

IDC-US Ref -2

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code ² (if known)		
MAU		US 4,786,140	A	11/22/1998	Melman
MAU		US 6,483,633	B2	11/19/2002	Okuno Onishi et al.
		US			
		US			

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation ⁴
		Country Code ³	Number ⁴	Kind Code ² (if known)			

IDC-Other Ref -4

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation ⁴
MAU		K. Suto et al, "Semiconductor Raman Amplifier for Terahertz Bandwidth Optical Communication", JOURNAL OF LIGHTWAVE TECHNOLOGY, IEEE, New York, US, Vol. 20, No. 4, April 2002, pp. 705-711, XP001130032	Yes
I		K. Suto et al, "Raman amplification in GaP-AlxGal-xP waveguides for light frequency discrimination", IEE PROCEEDINGS: OPTOELECTRONICS, INSTITUTION OF ELECTRICAL ENGINEERS, Stevenage, GB, Vol. 145, No. 2, April 20, 1998, pp. 105-108, XP006011337	Yes
I		T. Saito et al, "Gain of High-Intensity Pulse -Pumped Gap-Algap Waveguide Raman Amplifier", IEE PROCEEDINGS: OPTOELECTRONICS, INSTITUTION OF ELECTRICAL ENGINEERS, Stevenage, GB, Vol. 146, No. 5, October 1999, pp. 209-212, XP000928397	Yes
MAU		R. Claps et al, "Stimulated Raman scattering in silicon waveguides", ELECTRONICS LETTERS, IEE, Stevenage, GB, Vol. 38, No. 22, October 24 200, pp. 1352-1354, XP006019142	Yes

Examiner Signature

Mark Heller

Date Considered

10/14/2005

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² See Kind Codes of USPTO Patent Documents at www.uspto.gov, MPEP 901.04 or in the comment box of this document. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST. 3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to indicate here if English language Translation is attached.